SP Industrial
Reliable Embedded Partner

Datasheet

Industrial DRAM

DDR5 UDIMM Series



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Specifications Overview

- **Capacity**
  - 8GB, 16GB, 32GB
- **Form Factor**
  - DDR5 UDIMM
- **Performance**
  - 4800 = 38.4 GB/s
  - 5600 = 44.8 GB/s
- **Temperature Range**
  - Operation temperature:
    Normal temperature: -20°C ~ 95°C
    Wide temperature: -40°C ~ 105°C
- **Power Consumption**
  - Supply Voltage: DC +1.1V ± 5%
- **Compliant Specifications**
  - RoHS 2.0

RESTRICTIONS OF DATASHEET USE

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Revision History

Revision	Date	Description
1.0	2023/01	First Release
1.1	2023/06	Add DDR5 8GB (1Gx16) Update IDD Specification
1.2	2023/10	Add Hynix Solution Update Temperature Criterion Update IDD Specification
1.3	2023/11	Update Temperature Criterion
1.4	2023/12	Update Temperature
1.5	2024/12	Update Format Update Temperature Information Update Overview
1.6	2025/09	Add Nanya Solution
1.7	2025/11/12	Update Datasheet Format & Ordering Information Table
1.8	2025/12/05	Add CXMT Solution
1.9	2026/01/07	Update Ordering Information
2.0	2026/03/11	Add SP016GILVV480FH0
2.1	2026/03/19	Add Spectek Solution

1. Product Description

1.1 Overview

The Silicon Power Computer & Communications industrial DRAM products are JEDEC standard 288-Pin low power Double Data Rate 5 (DDR5) Synchronous DRAM Unbuffered Dual In-Line Memory Module (UDIMM) DDR5 UDIMM provide a high-performance, flexible 8-byte interface in a space-saving footprint. It is commonly used as the main memory in computers and other devices due to its cost-effectiveness and relatively high speed.

1.2 Features

- Fast data transfer rates:

Module Transfer Rates	Supported Transfer Rates	
	DDR5-4800(CL40)	DDR5-5600 (CL46)
DDR5-4800	V	
DDR5-5600	V	V

- Single or Dual rank
- $V_{DD} = V_{DDQ} = 1.1V \pm 0.06V$
- Fly-by topology
- Terminated clock, control and command/address
- Halogen-free
- Integrated serial presence-detect (SPD) EEPROM
- Gold edge contactsM

2. Specification

2.1 Physical Dimension

2.1.1 Dimension

Table 1: Physical Dimension

Parameter	Dimension
Length	133.35 ± 0.1mm
Width	31.25 ± 0.1mm
Thickness (connector)	1.27mm

2.1.2 Weight

- 1 Rank: 17.3g ± 10%
- 2 Ranks: 19.2g ± 10%

2.2 Performance

DDR5-4800 (PC5-38400)

DDR5-5600 (PC5-44800)

2.3 Environmental Conditions

Table 2: Environmental Conditions

Feature	Operating	Storage
Temperature (Normal Grade)	-20°C ~ 95°C	-55°C ~ 110°C
Temperature (Wide-Temperature Grade)	-40°C ~ 105°C	-55°C ~ 110°C
Humidity	10% ~ 95% RH, non-condensing	
Vibration	20G (Peak-to-Peak), 80~2000 Hz	
Shock	1,500G, 0.5ms	

Notice:

- Vibration: Duration, 30 min x 3 axis.
- Shock: 1500G, 0.5msec, half-sine wave, 3 times in each direction, total = 18 times (6 directions).
- Temperature: The temperature reading is for the environment defined as Ta.

2.4 Compliance Specifications

- RoHS

3. Functional Description

3.1 Pin Assignment

Table 3: Pin Assignment

288-Pin DDR5 UDIMM Front								288-Pin DDR5 UDIMM Back							
Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol
1	VIN_BULK	37	DQ20_A	73	CK0_A_c	109	V_{SS}	145	VIN_BULK	181	DQ22_A	217	CK1_A_c	253	V_{SS}
2	RFU	38	V_{SS}	74	V_{SS}	110	DQ5_B	146	VIN_BULK	182	V_{SS}	218	V_{SS}	254	DQ7_B
3	RFU	39	DQ21_A	75	RFU	111	V_{SS}	147	PWR_-GOOD	183	DQ23_A	219	RFU	255	V_{SS}
4	HSCL	40	V_{SS}	76	RFU	112	DQ8_B	148	HSA	184	V_{SS}	220	RFU	256	DQ10_B
5	HSDA	41	DQ24_A	77	V_{SS}	113	V_{SS}	149	RFU	185	DQ26_A	221	V_{SS}	257	V_{SS}
6	V_{SS}	42	V_{SS}	78	CK0_B_t	114	DQ9_B	150	V_{SS}	186	V_{SS}	222	CK1_B_t	258	DQ11_B
7	RFU	43	DQ25_A	79	CK0_B_c	115	V_{SS}	151	PWR_EN	187	DQ27_A	223	CK1_B_c	259	V_{SS}
8	V_{SS}	44	V_{SS}	80	V_{SS}	116	DM1_B_n	152	RFU	188	V_{SS}	224	V_{SS}	260	DQS1_B_c
9	DQ0_A	45	DM3_A_n	81	RFU	117	V_{SS}	153	V_{SS}	189	DQS3_A_c	225	RFU	261	DQS1_B_t
10	V_{SS}	46	V_{SS}	82	CA12_B	118	DQ12_B	154	DQ2_A	190	DQS3_A_t	226	RFU	262	V_{SS}
11	DQ1_A	47	DQ28_A	83	V_{SS}	119	V_{SS}	155	V_{SS}	191	V_{SS}	227	V_{SS}	263	DQ14_B
12	V_{SS}	48	V_{SS}	84	CA10_B	120	DQ13_B	156	DQ3_A	192	DQ30_A	228	CA11_B	264	V_{SS}
13	DQS0_A_c	49	DQ29_A	85	CA8_B	121	V_{SS}	157	V_{SS}	193	V_{SS}	229	CA9_B	265	DQ15_B
14	DQS0_A_t	50	V_{SS}	86	V_{SS}	122	DQ16_B	158	DM0_A_n	194	DQ31_A	230	V_{SS}	266	V_{SS}
15	V_{SS}	51	CB0_A	87	CA6_B	123	V_{SS}	159	V_{SS}	195	V_{SS}	231	CA7_B	267	DQ18_B
16	DQ4_A	52	V_{SS}	88	CA4_B	124	DQ17_B	160	DQ6_A	196	CB2_A	232	CA5_B	268	V_{SS}
17	V_{SS}	53	CB1_A	89	V_{SS}	125	V_{SS}	161	V_{SS}	197	V_{SS}	233	V_{SS}	269	DQ19_B
18	DQ5_A	54	V_{SS}	90	CA2_B	126	DQS2_B_c	162	DQ7_A	198	CB3_A	234	CA3_B	270	V_{SS}
19	V_{SS}	55	DQS4_A_c	91	CA0_B	127	DQS2_B_t	163	V_{SS}	199	V_{SS}	235	CA1_B	271	DM2_B_n
20	DQ8_A	56	DQS4_A_t	92	V_{SS}	128	V_{SS}	164	DQ10_A	200	ALERT_n	236	V_{SS}	272	V_{SS}
21	V_{SS}	57	V_{SS}	93	CS0_B_n	129	DQ20_B	165	V_{SS}	201	V_{SS}	237	CS1_B_n	273	DQ22_B
22	DQ9_A	58	CS0_A_n	94	V_{SS}	130	V_{SS}	166	DQ11_A	202	CS1_A_n	238	V_{SS}	274	V_{SS}
23	V_{SS}	59	V_{SS}	95	RESET_n	131	DQ21_B	167	V_{SS}	203	V_{SS}	239	DQS4_B_c	275	DQ23_B
24	DM1_A_n	60	CA0_A	96	V_{SS}	132	V_{SS}	168	DQS1_A_c	204	CA1_A	240	DQS4_B_t	276	V_{SS}
25	V_{SS}	61	CA2_A	97	CB0_B	133	DQ24_B	169	DQS1_A_t	205	CA3_A	241	V_{SS}	277	DQ26_B
26	DQ12_A	62	V_{SS}	98	V_{SS}	134	V_{SS}	170	V_{SS}	206	V_{SS}	242	CB2_B	278	V_{SS}
27	V_{SS}	63	CA4_A	99	CB1_B	135	DQ25_B	171	DQ14_A	207	CA5_A	243	V_{SS}	279	DQ27_B
28	DQ13_A	64	CA6_A	100	V_{SS}	136	V_{SS}	172	V_{SS}	208	CA7_A	244	CB3_B	280	V_{SS}
29	V_{SS}	65	V_{SS}	101	DQ0_B	137	DM3_B_n	173	DQ15_A	209	V_{SS}	245	V_{SS}	281	DQS3_B_c
30	DQ16_A	66	CA8_A	102	V_{SS}	138	V_{SS}	174	V_{SS}	210	CA9_A	246	DQ2_B	282	DQS3_B_t

288-Pin DDR5 UDIMM Front								288-Pin DDR5 UDIMM Back							
Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol
31	V_{SS}	67	CA10_A	103	DQ1_B	139	DQ28_B	175	DQ18_A	211	CA11_A	247	V_{SS}	283	V_{SS}
32	DQ17_A	68	V_{SS}	104	V_{SS}	140	V_{SS}	176	V_{SS}	212	V_{SS}	248	DQ3_B	284	DQ30_B
33	V_{SS}	69	CA12_A	105	DQS0_B_c	141	DQ29_B	177	DQ19_A	213	RFU	249	V_{SS}	285	V_{SS}
34	DQS2_A_c	70	RFU	106	DQS0_B_t	142	V_{SS}	178	V_{SS}	214	RFU	250	DM0_B_n	286	DQ31_B
35	DQS2_A_t	71	V_{SS}	107	V_{SS}	143	RFU	179	DM2_A_n	215	V_{SS}	251	V_{SS}	287	V_{SS}

3.2 Pin Description

Table 4: Pin Description

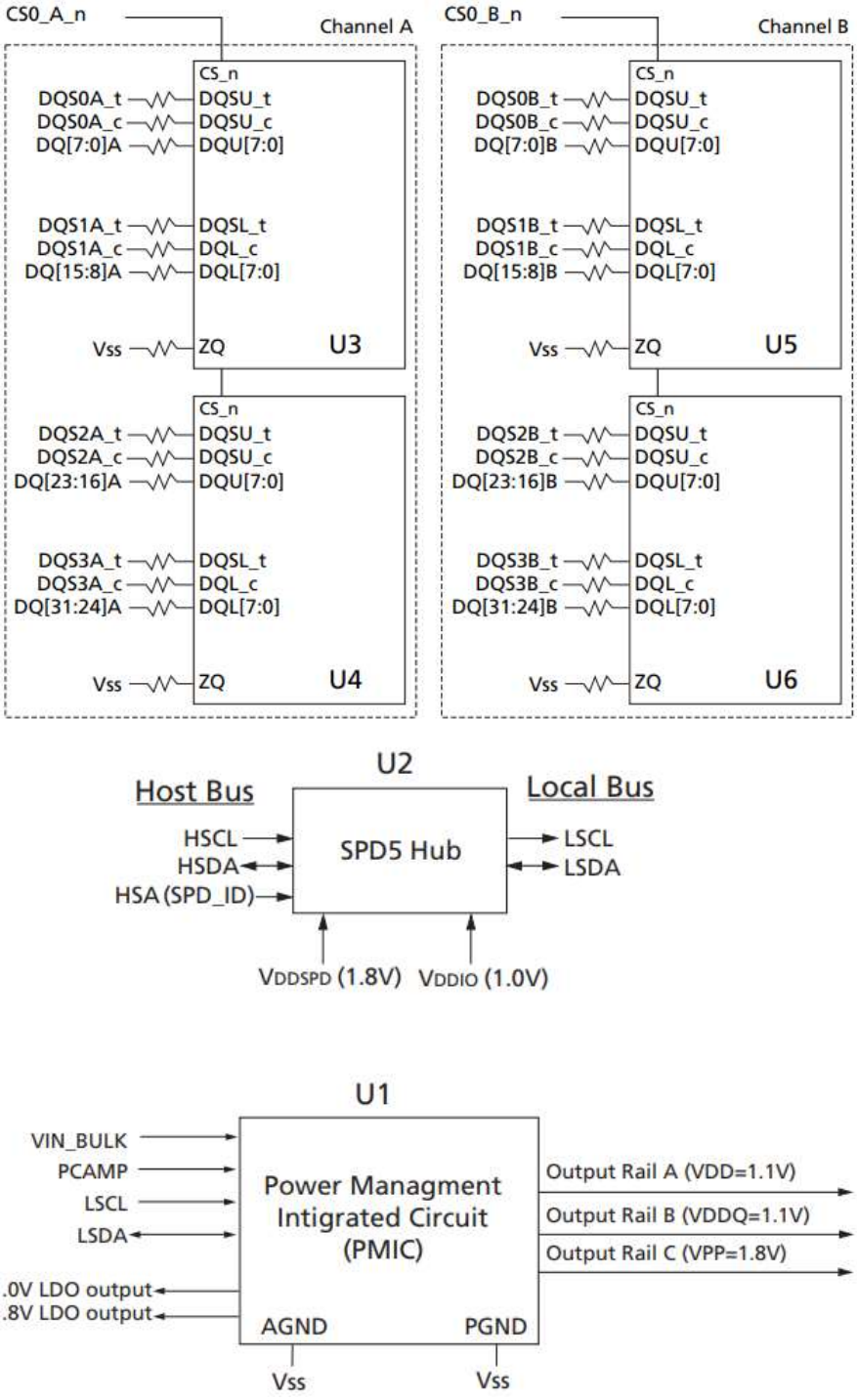
Symbol	Type	I/O Level	Description
CK[1:0]_A_t, CK[1:0]_B_t, CK[1:0]_A_c, CK[1:0]_B_c	Input	V_{DDQ}	**SDRAM Clocks** CK_t and CK_c are differential clock inputs. All address and con- trol input signals are sampled on the crossing of the positive edge of CK_t and negative edge of CK_c.
CA[12:0]_A CA[12:0]_B	Input	V_{DDQ}	**Command/Address Inputs:** CA signals provide the command and address inputs according to the Command Truth Table. Note that because some com- mands are multi-cycle, the pins may not be interchanged between devices on the same bus. The address inputs also provide the op-code during MODE REGISTER SET commands. The DDR5 component CA13 pin is strapped (connected) to either V_{SS} or V_{DDQ} depending on the strapped state of MIR.
CS[1:0]_A CS[1:0]_B	Input	V_{DDQ}	**Chip Select:** All commands are masked when CS_n is registered HIGH. CS_n pro- vides for external rank selection on systems with multiple ranks. CS_n is consid- ered part of the command code. CS_n is also used to enter and exit the parts from power down mode and self refresh mode. While not in self refresh mode the CS_n input buffer operates with the same ODT and V_{REF} parameters as config- ured by the CA_ODT strap setting or mode register. When in self refresh, the CS_n is a CMOS rail-to-rail signal with DC HIGH and LOW at 80% and 20% of V_{DD}.
ALERT_n	Outp ut	V_{DDQ}	**Alert:** If there is an error in CRC, then ALERT_n drives LOW for the period time interval and returns HIGH. During connectivity test mode, this pin functions as an input. Usage of this signal is system-dependent. In the case where this pin is not connected, ALERT_n must be bonded to V_{DDQ} on the system board.
RESET_n	CMOS Input	V_{DDQ}	**Active Low Asynchronous Reset:** Reset is active when RESET_n is LOW, and inactive when RESET_n is HIGH. RESET_n must be HIGH during normal operation. RESET_n is a CMOS rail-to-rail signal with DC HIGH and LOW at 80% and 20% of V_{DDQ}.
PWR_GOO D	Input Output	V_{DDQ}	**Power Good Indicator:** Open drain output. The PMIC ensures this pin HIGH when VIN_Bulk input supply, as well as all enabled output buck regulators and all LDO regulators tolerance threshold is maintained as configured in the appropri- ate register. The PMIC drives this pin LOW when VIN_Bulk input goes below the threshold or when any of the enabled output buck regulator exceeds the thresh- olds configured in the appropriate register or when any LDO output regulator exceeds the threshold configured in the appropriate register. As an input, the PMIC disables its output regulator when this pin is LOW. The LDO outputs remain on.

Symbol	Type	I/O Level	Description
HSCL	Input	VOUT_1.8V or VOUT_1.0V	**Host Sideband Bus Clock:** Bus clock used to strobe data into HUB device. When open drain, a pull-up resistor is required on the system motherboard.
HSDA	Input / Output	VOUT_1.8V or UT_1.0V	**Host Sideband Bus Data:**I2C/I3C-Basic data. When open drain, a pull-up resis- tor is required on the system motherboard.
HSA	Input	GND	**Host Sideband Bus Device ID**: Address input to a hub or other client device to distinguish between identical devices in the I3C basic address range. Tied to GND, HSA has different resistor values on the motherboard to identify DIMM slot address. Refer to the SPD Hub spec for more information.
DQ[31:0]_A DQ[31:0]_B	Input/ Output	V_{DDQ}	**Data Input/Output:** Bidirectional data bus. If CRC is enabled via the mode regis- ter, then CRC code is added at the end of data burst. Any DQ from DQ0–DQ3 may indicate the internal VREF level during test via mode register setting MR4 A4 = HIGH. Refer to the vendor-specific data sheets to determine which DQ is used.
CB[3:0]_A CB[3:0]_B	Input/ Output	V_{DDQ}	ECC Check Bits Input/Output: Bidirectional data bus. Only applicable on ECC SODIMM (SOEDIMM) or UDIMM (EUDIMM).
DQS[4:0]_A_t DQS[4:0]_B_t	Input/ Output	V_{DDQ}	**Data Strobe**: Output with read data, input with write data. Edge-aligned with read data, centered in write data. The data strobe DQS_t is paired with differen- tial signals DQS_c, respectively, to provide differential pair signaling to the system during reads and writes. DDR5 SDRAM only supports differential data strobe. It does not support single-ended strobe.
DQS[4:0]_A_c DQS[4:0]_B_c			
DM[3:0]_A_n DM[3:0]_B_n	Input	VDDQ	**Input Data Mask**: DM_n is an input mask signal for write data. Input data is masked when DM_n is sampled LOW coincident with that input data during a write access. DM_n is sampled on both edges of DQS. DM function is shared with TDQS on x8 devices. The function of DM_n is enabled by MR5:OP[5] = 1. Refer to Micron DDR5 component data sheet specification for further detail.
VIN_BULK	Supply		**External Power Supply**: 5V, 4.25V (min), 5.5V (max)
PWR_EN	Input		**PMIC Enable**: When this pin is HIGH, the PMIC turns on the regulator. When this pin is LOW, the PMIC turns off the regulator. This signal is connected to the PMIC's VR_EN pin.
VSS	Supply		Ground

Symbol	Type	I/O Level	Description
RFU			Reserved for future use. No on DIMM electrical connection is present.
NC			No connect: No internal electrical connection is present.
NF			No function: May have internal connection present, but has no function.

4. Block Diagram & Simplified Mechanical Drawing

4.1 Block Diagram (x16 1 Rank without ECC)

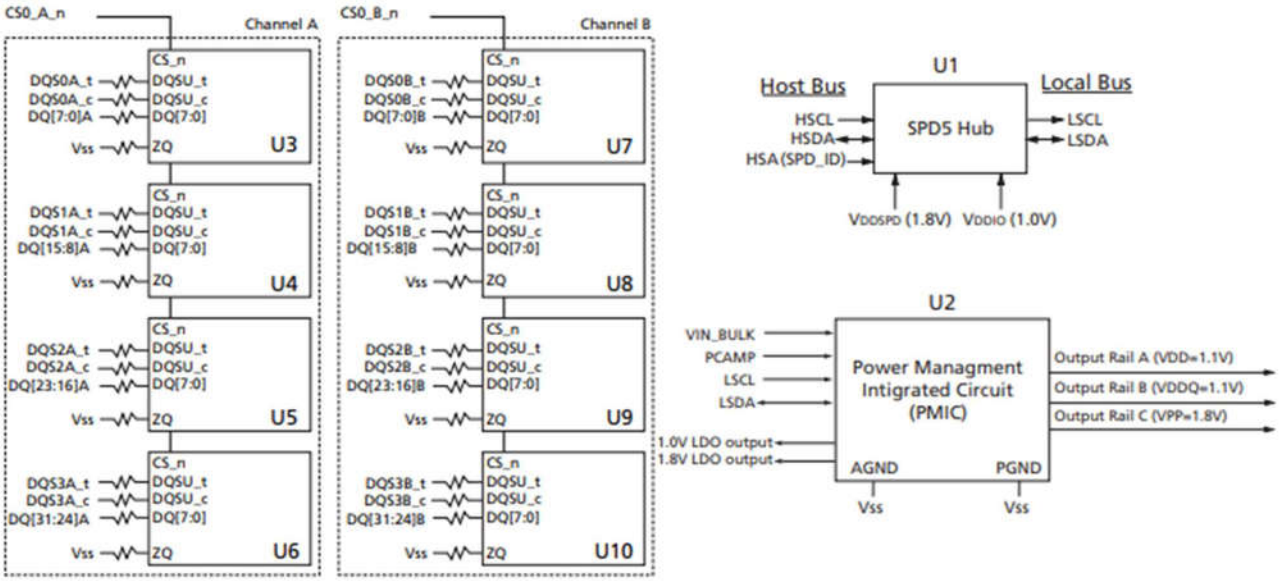


Note:

1. The ZQ ball on each DDR5 component is connected to an external 240Ω ±1% resistor that is tied to ground. It is used for the calibration of the component's ODT and output driver.

2. Functional block diagram is for reference only.

4.2 Block Diagram (x8 1 Rank without ECC)

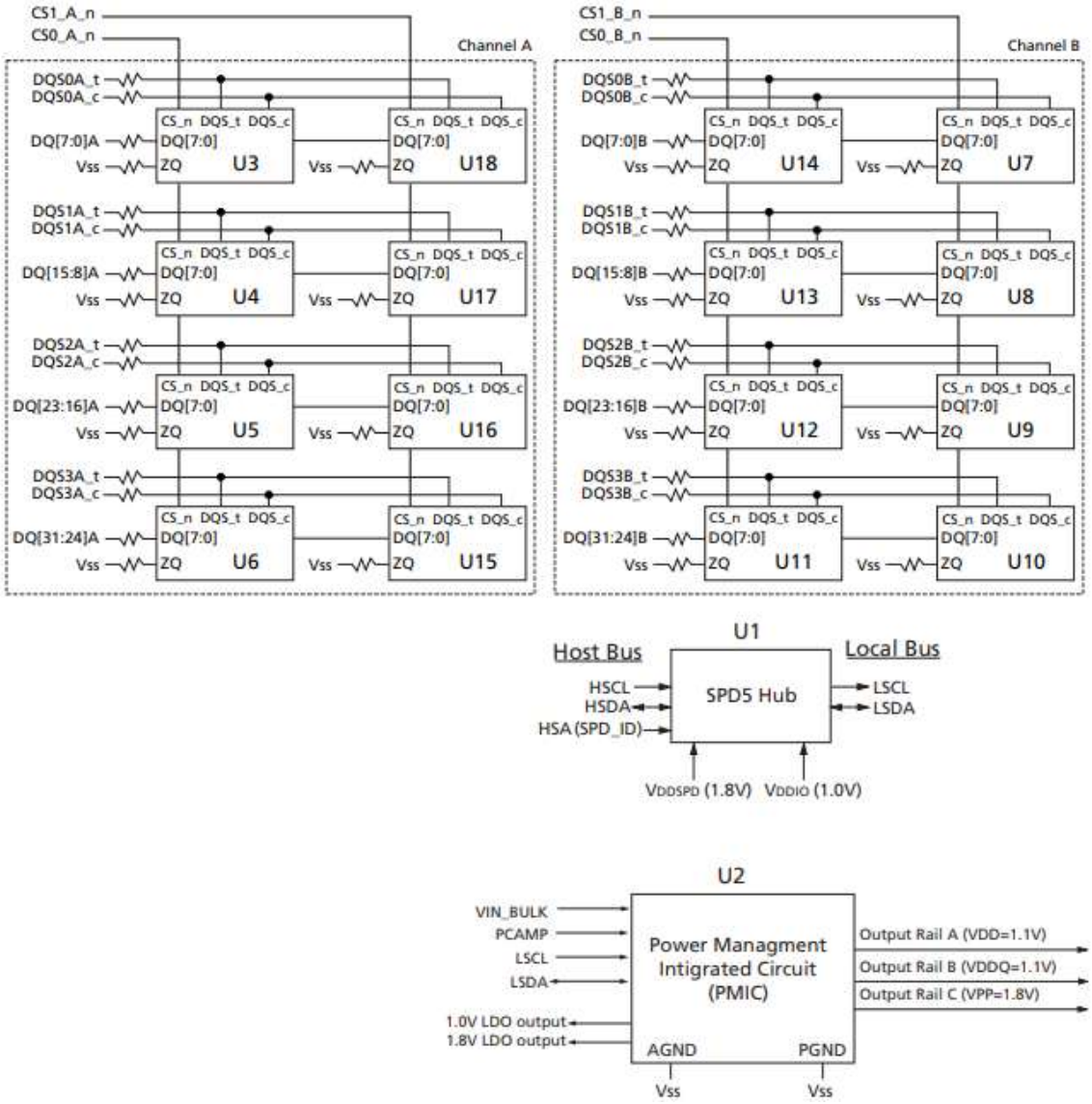


Note:

1. The ZQ ball on each DDR5 component is connected to an external 240Ω ±1% resistor that is tied to ground. It is used for the calibration of the component's ODT and output driver.

2. Functional block diagram is for reference only.

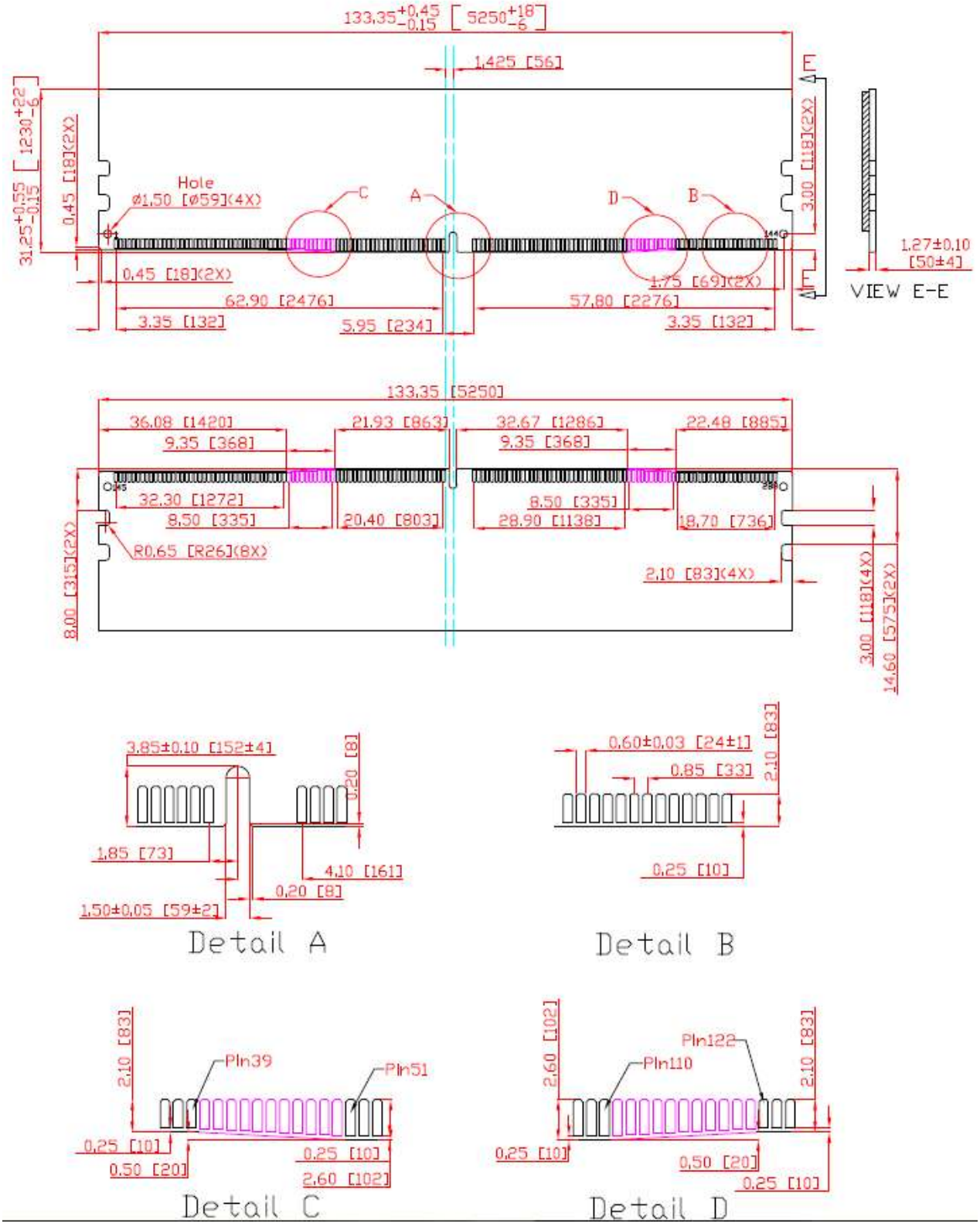
4.3 Block Diagram (x8 2 Ranks without ECC)



Notes:

1. The ZQ ball on each DDR5 component is connected to an external 240Ω ±1% resistor that is tied to ground. It is used for the calibration of the component's ODT and output driver.
2. Functional block diagram is for reference only.

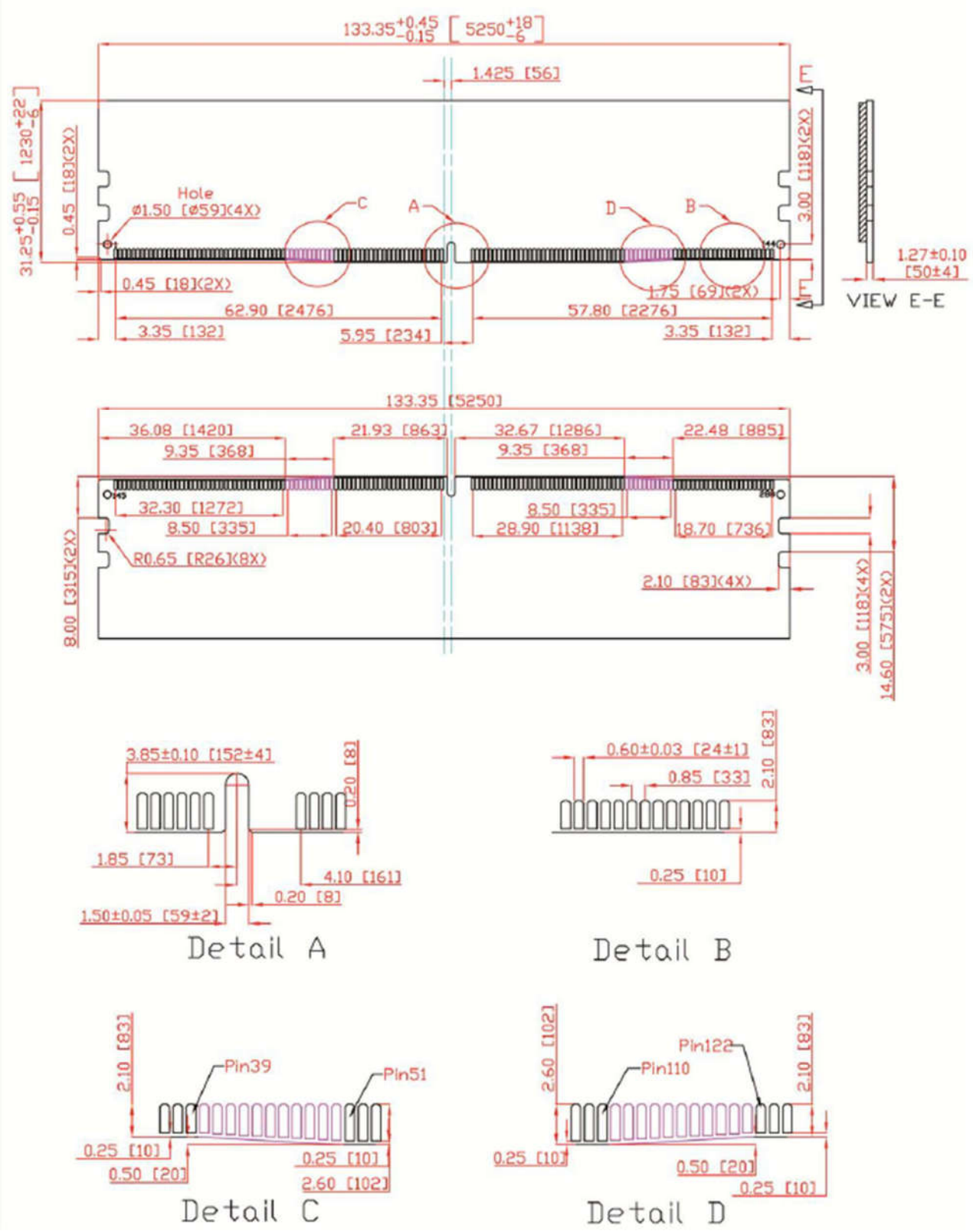
4.4 Simplified Mechanical Drawing (64bits UDIMM x16 1 Rank)



Notes:

1. All dimensions are in millimeters (inches); MAX/MIN or typical (TYP) where noted.
2. The dimensional diagram is for reference only.

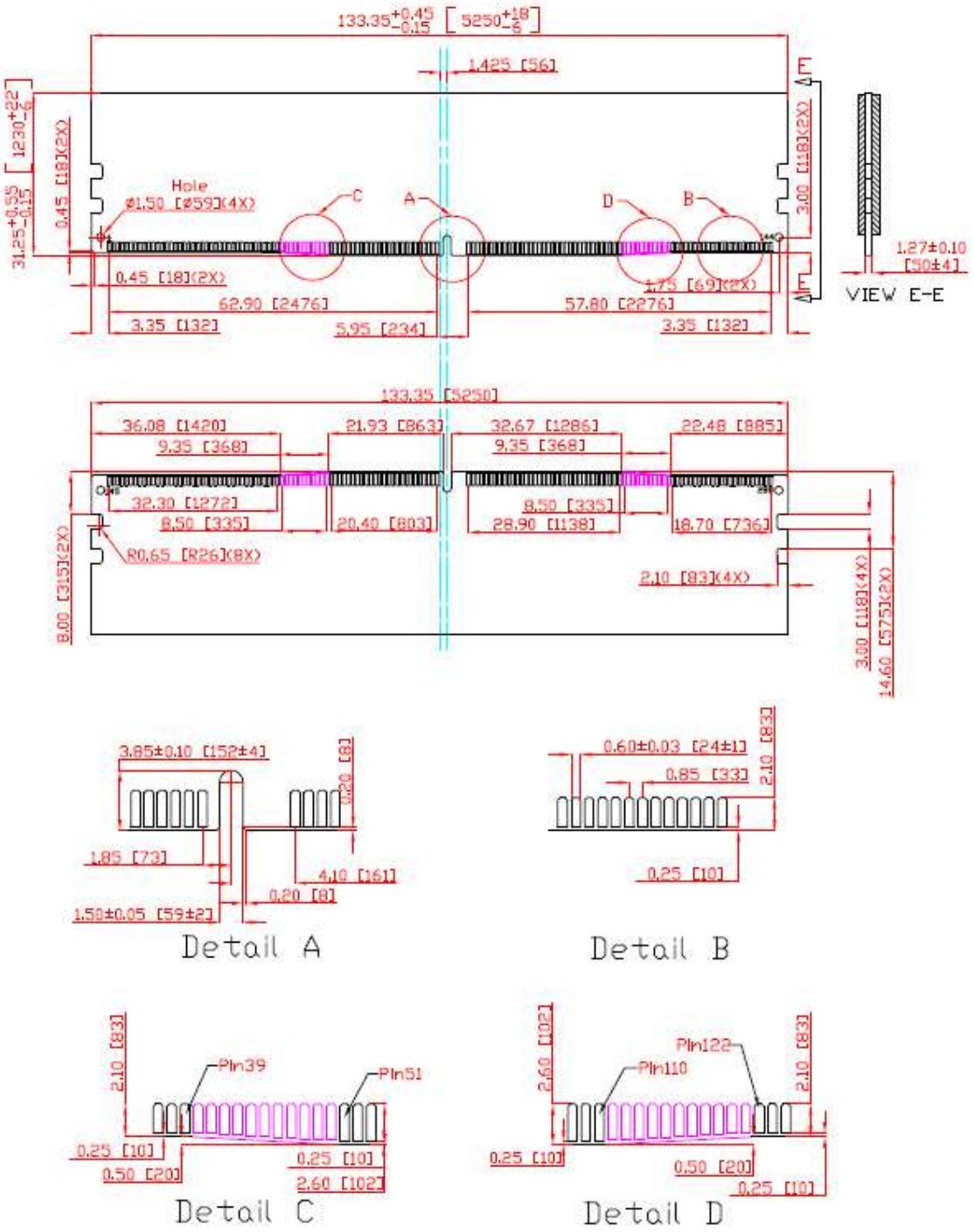
4.5 Simplified Mechanical Drawing (64bits UDIMM x8 1 Rank)



Notes:

1. All dimensions are in millimeters (inches); MAX/MIN or typical (TYP) where noted.
2. The dimensional diagram is for reference only.

4.6 Simplified Mechanical Drawing (64bits UDIMM x8 2 Ranks)



Notes:

1. All dimensions are in millimeters (inches); MAX/MIN or typical (TYP) where noted.

2. The dimensional diagram is for reference only.

5. Ordering Information

5.1 Part Number Definition

Table 5: Part Number Definition

Code	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
	S	P	0	3	2	G	I	L	V	V	5	6	0	F	H	0

Code 1-2: Brand	SP: Silicon Power
Code 3-6: Capacity	008G: 8GB; 016G: 16GB; 032G: 32GB
Code 7: Product	I: Industrial Product Line
Code 8-9: Type & Form Factor	L: UDIMM; V: DDR5
Code 10: Operation Temperature	U: Normal Temperature -20°C ~ 95°C V: Wide Temperature -40°C ~ 105°C
Code 11-13: Model Series	480: 4800; 560: 5600
Code 14: Series	G: 1Gx16 F: 2Gx8
Code 15: DRAM Vendor Brand	H: Hynix; N: Nanya; 2: CXMT; T: Spectek
Code 16: Reserved	0: Standard
Code 17-18 (Option)	For Customization

5.2 Ordering Information Table

Capacity	Part Number	Module Density & Configuration	Bandwidth	Data Rate	Timing
Normal Temperature (-20°C ~ 95°C)					
8GB	SP008GILVU480GM0	8GB (1Gbx64) 1Gx16, 1 Rank	38.4GB/s	DDR5-4800	40-39-39
	SP008GILVU560GH0	8GB (1Gbx64) 1Gx16, 1 Rank	44.8GB/s	DDR5-5600	46-45-45
	SP008GILVU560GN0	8GB (1Gbx64) 1Gx16, 1 Rank	44.8GB/s	DDR5-5600	46-45-45
	SP008GILVU560GT0	8GB (1Gbx64) 1Gx16, 1 Rank	44.8GB/s	DDR5-5600	46-45-45
16GB	SP016GILVU480FH0	16GB (2Gbx64) 2Gx8, 1 Rank	38.4GB/s	DDR5-4800	40-39-39
	SP016GILVU560FH0	16GB (2Gbx64) 2Gx8, 1 Rank	44.8GB/s	DDR5-5600	46-45-45
	SP016GILVU560FT0	16GB (2Gbx64) 2Gx8, 1 Rank	44.8GB/s	DDR5-5600	46-45-45

Capacity	Part Number	Module Density & Configuration	Bandwidth	Data Rate	Timing
	SP016GILVU560F20	16GB (2Gbx64) 2Gx8, 1 Rank	44.8GB/s	DDR5-5600	46-45-45
32GB	SP032GILVU480FH0	32GB (4Gbx64) 2Gx8, 2 Ranks	38.4GB/s	DDR5-4800	40-39-39
	SP032GILVU560FH0	32GB (4Gbx64) 2Gx8, 2 Ranks	44.8GB/s	DDR5-5600	46-45-45
Wide Temperature (-40°C ~ 105°C)					
8GB	SP008GILVV560GH0	8GB (1Gbx64) 1Gx16, 1 Rank	44.8GB/s	DDR5-5600	46-45-45
	SP008GILVV560GN0	8GB (1Gbx64) 1Gx16, 1 Rank	44.8GB/s	DDR5-5600	46-45-45
16GB	SP016GILVV480FH0	16GB (2Gbx64) 2Gx8, 1 Rank	38.4GB/s	DDR5-4800	40-39-39
	SP016GILVV560FH0	16GB (2Gbx64) 2Gx8, 1 Rank	44.8GB/s	DDR5-5600	46-45-45
32GB	SP032GILVV480FH0	32GB (4Gbx64) 2Gx8, 2 Ranks	38.4GB/s	DDR5-4800	40-39-39
	SP032GILVV560FH0	32GB (4Gbx64) 2Gx8, 2 Ranks	44.8GB/s	DDR5-5600	46-45-45

5.3 Appendix

Table 6: Abbreviation

Item	Abbreviation	Description
1	MTBF	Mean Time Between Failures
2	ECC	Error Correction Code
3	TCG	Trusted Computing Group
4	AES	Advanced Encryption Standard
5	OP	Over Provisioning
6	PS	Power Shield
7	DC	Direct Current
8	DRAM	Dynamic Random Access Memory
9	WAF	Write Amplification Factor
10	WLE	Wear Leveling Efficiency
11	Ta	Ambient Temperature
12	LBA	Logical Block Address

Contact Information

Silicon Power Computer & Communications Incorporation, a solid state memory or storage business company, provides total solutions in the design and marketing of SSD, Flash Module, and Industry Card products. For further supporting or detail information related to the products, please inform us through the following contact email address: isupport@silicon-power.com. We will response the requests soon.